



DMN2400UFB4

N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Ultra-Low Package Profile, 0.4mm Maximum Package Height
- Lead Free By Design/RoHS Compliant (Note 1)
- ESD Protected up to 1.5kV
- "Green" Device (Note 2)
- Qualified to AEC-Q101 standards for High Reliability

Mechanical Data

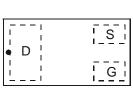
- Case: DFN1006H4-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: Collector Dot
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.001 grams (approximate)

DFN1006H4-3

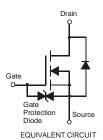




BOTTOM VIEW



TOP VIEW Package Pin Configuration



Ordering Information (Note 3)

Part Number	Case	Packaging
DMN2400UFB4-7	DFN1006H4-3	3000/Tape & Reel

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

Marking Information



NC = Product Type Marking Code Dot Denotes Drain Side



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	20	V		
Gate-Source Voltage	V_{GSS}	±12	V		
Continuous Drain Current (Note 4) V _{GS} = 4.5V	Steady State	T _A = 25°C T _A = 85°C	I _D	0.75 0.55	А
Pulsed Drain Current (Notes 4 & 5)	I _{DM}	3	А		

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	P_{D}	0.47	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	258	°C/W
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C

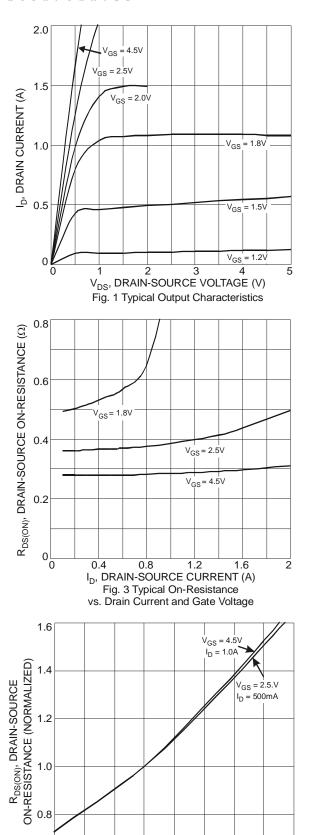
Electrical Characteristics @TA = 25°C unless otherwise specified

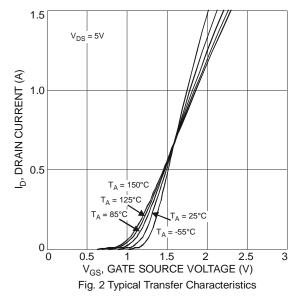
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	100	nA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±1.0	μΑ	$V_{GS} = \pm 4.5 V, V_{DS} = 0 V$	
Gate-Source Leakage	I _{GSS}	-	-	±50	μΑ	$V_{GS} = \pm 10V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(th)}	0.5	-	0.9	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
		-	-	0.55	Ω	$V_{GS} = 4.5V, I_D = 600mA$	
Static Drain-Source On-Resistance	R _{DS} (ON)	1	-	0.75		$V_{GS} = 2.5V, I_D = 500mA$	
		-	-	0.9		$V_{GS} = 1.8V, I_D = 350mA$	
Forward Transfer Admittance	Y _{fs}	-	1.0	-	S	$V_{DS} = 10V, I_D = 400mA$	
Diode Forward Voltage (Note 6)	V _{SD}		0.7	1.2	V	$V_{GS} = 0V, I_{S} = 150mA$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}	-	36.0	-	pF	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Output Capacitance	Coss	-	5.7	-	pF	$V_{DS} = 16V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	1	4.2	-	pF		
Total Gate Charge	Q_g	-	0.5	-	nC	V _{GS} =4.5V, V _{DS} = 10V, ID =250mA	
Gate-Source Charge	Q_{gs}	-	0.07	-	nC		
Gate-Drain Charge	Q_{gd}	-	0.1	-	nC		
Turn-On Delay Time	t _{D(on)}	-	4.11	-	ns	$V_{DD} = 10V$, $V_{GS} = 4.5V$, $R_L = 47\Omega$, $R_G = 10\Omega$, $I_D = 200 \text{mA}$	
Turn-On Rise Time	t _r	-	3.82	-	ns		
Turn-Off Delay Time	t _{D(off)}	-	14.8	-	ns		
Turn-Off Fall Time	t _f	-	9.6	-	ns		

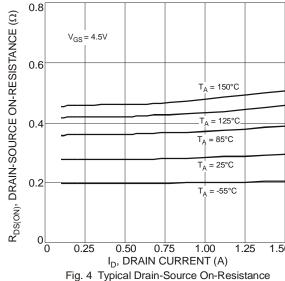
Notes:

- 4. Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided.
- 5. Device mounted on minimum recommended pad layout test board, 10μs pulse duty cycle = 1%.
- 6. Short duration pulse test used to minimize self-heating effect.
- 7. Guaranteed by design. Not subject to product testing.









vs. Drain Current and Temperature

50

T_J, JUNCTION TEMPERATURE (°C)

Fig. 5 On-Resistance Variation with Temperature

75

100

25

125 150

0.6

-50



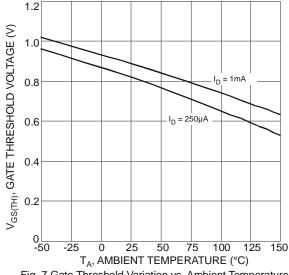
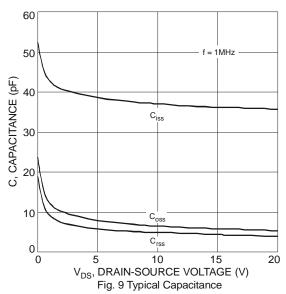
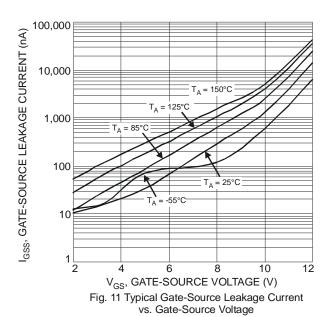
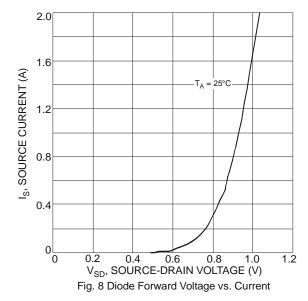
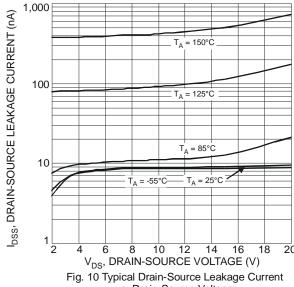


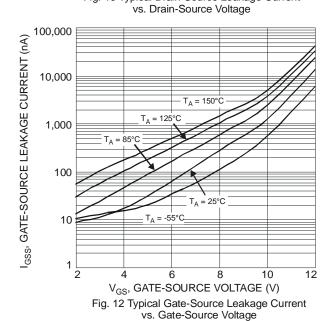
Fig. 7 Gate Threshold Variation vs. Ambient Temperature



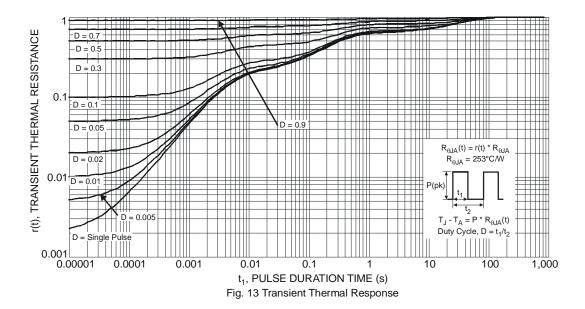




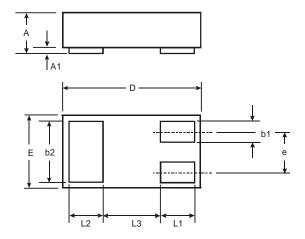






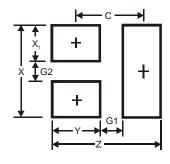


Package Outline Dimensions



DFN1006H4-3					
Dim	Min	Max	Тур		
Α		0.40			
A1	0	0.05	0.02		
b1	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
Е	0.55	0.675	0.60		
е	_	_	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	_	_	0.40		
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
Х	0.7
X1	0.25
Y	0.4
С	0.7



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